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FGA180N33AT 330V, 180A PDP Trench IGBT

Features

- High Current Capability
- + Low saturation voltage: V_{CE(sat)} =1.03V @ I_C = 40A
- High input impedance
- · RoHS compliant

Applications

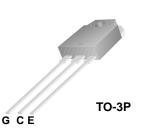
PDP SYSTEM

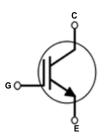


General Description

Using Novel Trench IGBT Technology, Fairchild's new series of trench IGBTs offer the optimum performance for PDP applications where low conduction and switching losses are essential.

April 2008





Absolute Maximum Ratings

Symbol	Description		Ratings	Units	
V _{CES}	Collector to Emitter Voltage		330	V	
V _{GES}	Gate to Emitter Voltage		± 30	V	
I _C	Collector Current	@ T _C = 25°C	180	А	
I _{C pulse (1)}	Pulsed Collector Current	@ T _C = 25°C	450	А	
P _D	Maximum Power Dissipation	@ T _C = 25°C	390	W	
. D	Maximum Power Dissipation	@ T _C = 100 ^o C	156	W	
TJ	Operating Junction Temperature		-55 to +150	°C	
T _{stg}	Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Notes:

1: Repetitive test, pulse width = 100usec, Duty = 0.1

* I_C pulse limited by max Tj

Thermal Characteristics

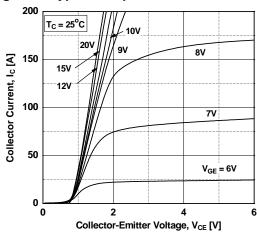
Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.32	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	-	40	°C/W

				Packaging			Max ()tv nei	
Device Marking FGA180N33AT		Device	Package	ackage Type		Qty per Tube		Max Qty per Box	
		FGA180N33ATTU	TO-3P	Tube	30ea			-	
Electric	al Char	acteristics of the					I		
Symbol		Parameter	-	Conditions	Min.	Тур.	Max.	Units	
011 01									
Off Charac		to Emitter Breekdown Valter		2504	220	-	-	V	
BV _{CES}		to Emitter Breakdown Voltag	02 0		330	-			
ICES		Cut-Off Current		$E = V_{CES}, V_{GE} = 0V$ $E = V_{GES}, V_{CE} = 0V$		-	250	μA	
I _{GES}	G-E Leak	age Current	VGE = VGES	, v _{CE} = 0v	-	-	±400	nA	
On Charac	teristics								
V _{GE(th)}	G-E Three	shold Voltage	I _C = 250uA,	V _{CE} = V _{GE}	2.5	4.0	5.5	V	
- ()			I _C = 40A, V _G	_E = 15V	-	1.1	1.4	V	
	Collector	to Emitter Saturation Voltage	I _C = 180A, V	_{GE} = 15V,	-	1.68	-	V	
V _{CE(sat)} Collector to Emitter Saturation Voltage			I _C = 180A, V _{GE} = 15V T _C = 125°C		1.89	_	V		
Dynamic C	haracteris	tics	I		-	1		L	
C _{ies}	Input Cap	acitance			-	3880	-	pF	
C _{oes}	Output Ca	apacitance		V _{CE} = 30V, V _{GE} = 0V, f = 1MHz		305	-	pF	
<u>^</u>	Boyoroo T					180	_	pF	
C _{res}	Reveise	Fransfer Capacitance			-				
								I	
Switching	Characteri	stics				1		ne	
Switching t _{d(on)}	Characteri Turn-On [stics Delay Time	V _{CC} = 200V	, I _C = 40A,	-	27	-	ns	
Switching t _{d(on)} t _r	Characteri Turn-On I Rise Time	stics Delay Time	$-R_{G} = 5\Omega, V_{C}$	_{GE} = 15V,	-	27 80	-	ns	
Switching t _{d(on)} t _r t _{d(off)}	Characteri Turn-On [Rise Time Turn-Off [stics Delay Time	$-R_{G} = 5\Omega, V_{C}$	$I_{\rm C} = 40$ A, $S_{\rm E} = 15$ V, ad, T _C = 25°C	-	27 80 108	-	ns ns	
Switching t _{d(on)} t _r t _{d(off)} t _f	Characteri Turn-On I Rise Time Turn-Off I Fall Time	stics Delay Time Delay Time	$-R_{G} = 5\Omega, V_{C}$	_{GE} = 15V,	- - -	27 80 108 180	- 240	ns ns ns	
$\frac{\text{Switching}}{t_{d(on)}}$ $\frac{t_r}{t_{d(off)}}$ $\frac{t_f}{t_{d(on)}}$	Characteri Turn-On [Rise Time Turn-Off [Fall Time Turn-On [stics Delay Time Delay Time Delay Time	$R_{G} = 5\Omega, V_{C}$ Resistive Lo	$_{BE} = 15V,$ ad, $T_{C} = 25^{\circ}C$, $I_{C} = 40A,$	- - - -	27 80 108 180 26	-	ns ns ns ns	
Switching td(on) tr td(off) tf td(on) tr	Characteri Turn-On I Rise Time Turn-Off I Fall Time Turn-On I Rise Time	stics Delay Time Delay Time Delay Time	$R_{G} = 5\Omega, V_{C}$ Resistive LC $V_{CC} = 200V$ $R_{G} = 5\Omega, V_{C}$	$_{BE} = 15V,$ ad, $T_{C} = 25^{\circ}C$, $I_{C} = 40A,$ $_{BE} = 15V,$	- - - -	27 80 108 180 26 75	- 240	ns ns ns ns ns	
Switching $t_{d(on)}$ t_r $t_{d(off)}$ t_f $t_{d(on)}$ t_r $t_{d(off)}$	Characteri Turn-On I Rise Time Turn-Off I Fall Time Turn-On I Rise Time Turn-Off I	stics Delay Time Delay Time Delay Time	$R_{G} = 5\Omega, V_{C}$ Resistive LC $V_{CC} = 200V$ $R_{G} = 5\Omega, V_{C}$	$_{BE} = 15V,$ ad, $T_{C} = 25^{\circ}C$, $I_{C} = 40A,$	- - - - -	27 80 108 180 26 75 112	- 240 - -	ns ns ns ns ns ns	
$\frac{\text{Switching}}{t_{d(on)}}$ $\frac{t_{r}}{t_{d(off)}}$ $\frac{t_{f}}{t_{d(on)}}$ $\frac{t_{r}}{t_{r}}$ $\frac{t_{d(off)}}{t_{f}}$	Characteri Turn-On I Rise Time Turn-Off I Fall Time Turn-On I Rise Time Turn-Off I Fall Time	stics Delay Time Delay Time Delay Time Delay Time	$R_{G} = 5\Omega, V_{C}$ Resistive LC $V_{CC} = 200V$ $R_{G} = 5\Omega, V_{C}$	$_{BE} = 15V,$ ad, $T_{C} = 25^{\circ}C$, $I_{C} = 40A,$ $_{BE} = 15V,$	- - - - - -	27 80 108 180 26 75 112 250	- 240	ns ns ns ns ns ns ns	
Switching t _{d(on)} t _r t _{d(off)} t _f	Characteri Turn-On I Rise Time Turn-Off I Fall Time Turn-On I Rise Time Turn-Off I Fall Time Total Gate	stics Delay Time Delay Time Delay Time Delay Time	$R_{G} = 5\Omega, V_{C}$ Resistive LC $V_{CC} = 200V$ $R_{G} = 5\Omega, V_{C}$	$_{BE} = 15V,$ $_{DC} = 25^{\circ}C$ $_{DC} = 40A,$ $_{BE} = 15V,$ $_{DC} = 125^{\circ}C$	- - - - - -	27 80 108 180 26 75 112	- 240 - -	ns ns ns ns ns ns	

FGA180N33AT 330V, 180A PDP Trench IGBT

Typical Performance Characteristics

Figure 1. Typical Output Characteristics





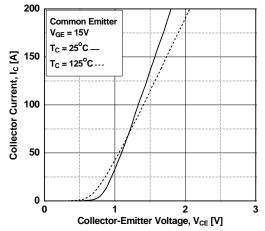


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

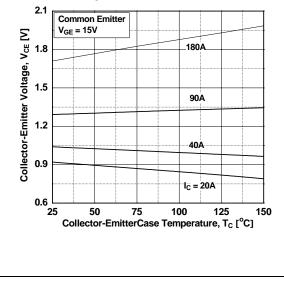


Figure 2. Typical Output Characteristics

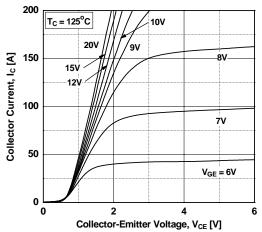


Figure 4. Transfer Characteristics

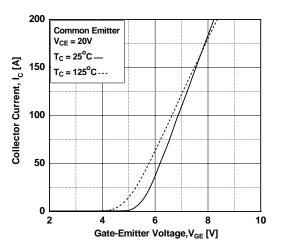
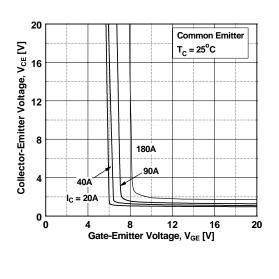


Figure 6. Saturation Voltage vs. V_{GE}



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Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

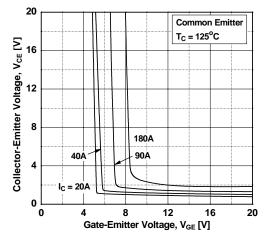


Figure 9. Gate charge Characteristics

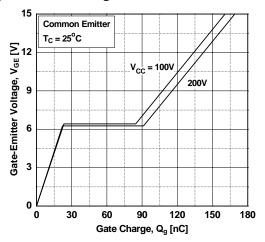
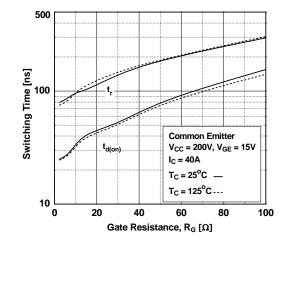
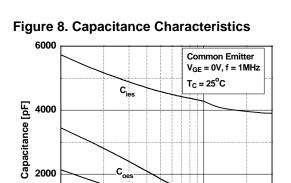


Figure 11. Turn-on Characteristics vs. Gate Resistance





C_{res}

0

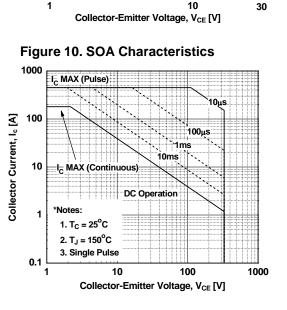
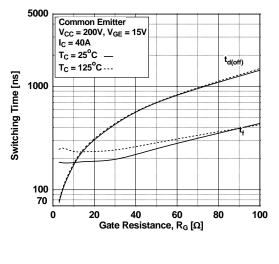


Figure 12. Turn-off Characteristics vs. Gate Resistance



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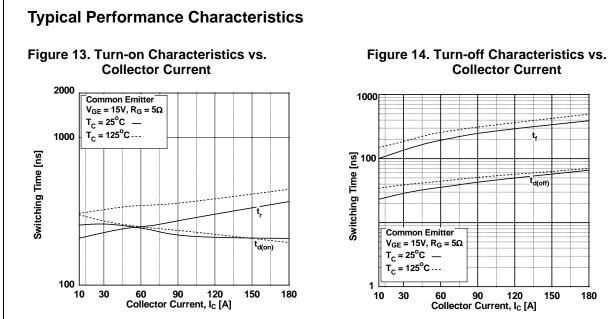
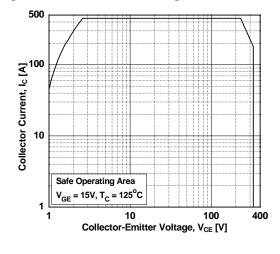
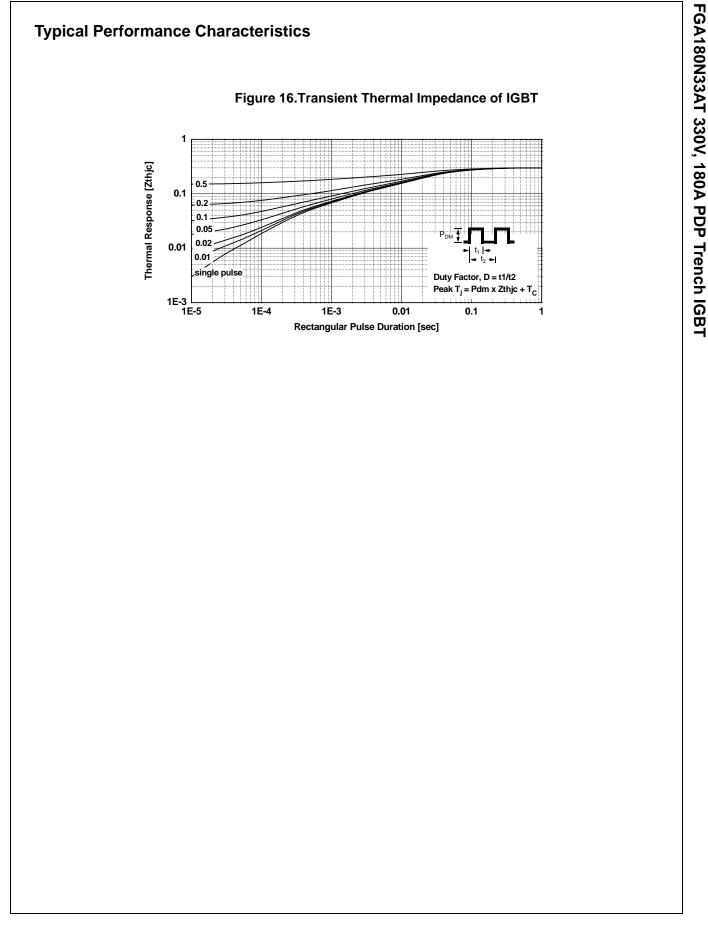


Figure 15. Turn off Switching SOA Characteristics

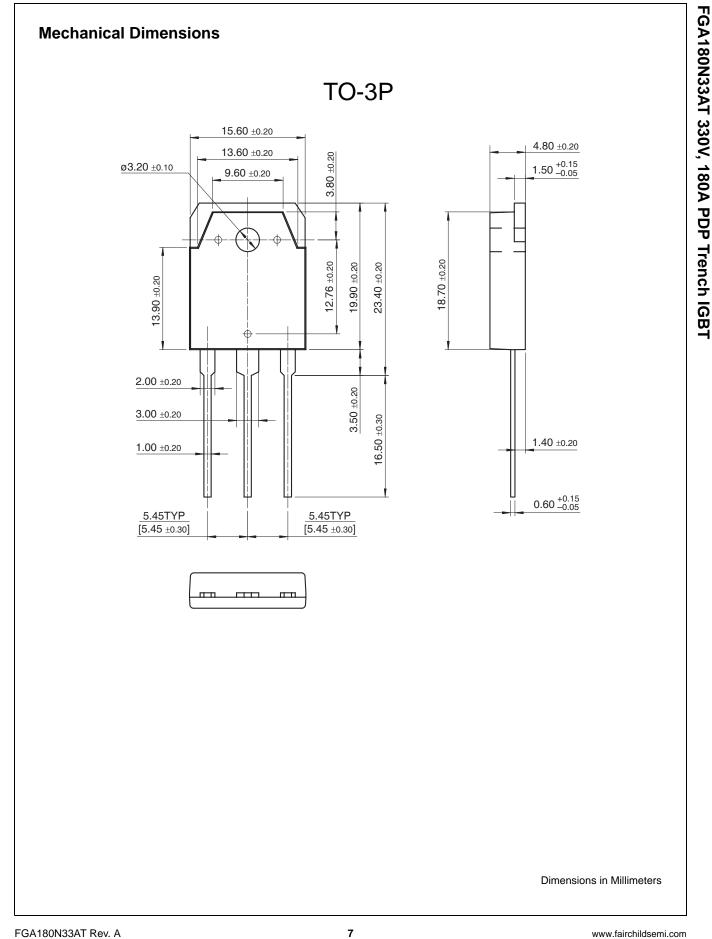


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